ELSEVIER

Journal of Crystal Growth 212 (2000) 608–614

JOURNAL OF CRYSTAL GROWTH

www.elsevier.nl/locate/jcrysgro

Author index

Adamowicz, L., see Kamler, G. 212 (2000) 39

Asthagiri, D., A.M. Lenhoff and D.T. Gallagher, Role of competitive interactions in growth rate trends of subtilisin s88 crystals 212 (2000) 543

Atanassova, S., K. Neykov and I. Gutzow, Solubility and dissolution kinetics of calcium oxalate renal calculi in solutions, containing DL-lysine: in vitro experiments 212 (2000) 233

Bacher, A., see Braun, N. 212 (2000) 270

Bachmann, L., see Braun, N. 212 (2000) 270

Balakrishnan, K., see Iida, S. 212 (2000) 601

Balic-Zunic, T., see Christoffersen, M.R. 212 (2000) 500

Balitsky, V.S., I.B. Machina, A.A. Mar'in, J.E. Shigley, G.R. Rossman and T. Lu, Industrial growth, morphology and some properties of Bi-colored amethyst–citrine quartz (ametrine) 212 (2000) 255

Baskar, K., see Jeganathan, K. 212 (2000) 29

Beatty, K.M., see Shneidman, V.A. 212 (2000) 564

Belaya, A.D., see Zemskov, V.S. 212 (2000) 161

Bello, I., see Zhang, Y.F. 212 (2000) 115

Beluy, U.S., see Zemskov, V.S. 212 (2000) 161

Bender, H., see Jin, S. 212 (2000) 119

Bergmaier, A., see Vogg, G. 212 (2000) 148

Bhuiyan, A.G., A. Hashimoto, A. Yamamoto and R. Ishigami, Nitridation effects of GaP(1 1 1)B substrate on MOCVD growth of InN 212 (2000) 379

Bilyalov, R., see Jin, S. 212 (2000) 119

Boateng, K.A., see Mohan, R. 212 (2000) 489

Brandt, M.S., see Vogg, G. 212 (2000) 148

Braun, N., J. Tack, M. Fischer, A. Bacher, L. Bachmann and S. Weinkauf, Electron microscopic observations on protein crystallization: adsorption layers, aggregates and crystal defects 212 (2000) 270

Caymax, M., see Jin, S. 212 (2000) 119

Chai, C., see Xu, M. 212 (2000) 291

Chani, V.I., A. Yoshikawa, H. Machida and T. Fukuda, Melt growth of $(Tb,Lu)_3Al_5O_{12}$ mixed garnet fiber crystals 212 (2000) 469

Chen, F., see Lu, H.B. 212 (2000) 173

Chen, F., see Zhao, T. 212 (2000) 451

Chen, H., see Zhang, S. 212 (2000) 217

Chen, H., see Liu, H. 212 (2000) 391

Chen, H., see Zhang, S. 212 (2000) 476

Chen, J.-C., see Lai, Y.-J. 212 (2000) 211

Chen, N.T., see Yokoyama, M. 212 (2000) 97

Chen, W.Z., see Lu, H.B. 212 (2000) 173

Chen, Y.-H., see Sun, Z.-Z. 212 (2000) 360

Chen, Z., see Zhao, T. 212 (2000) 451

Cheng, Z., see Zhang, S. 212 (2000) 217

Cheng, Z., see Zhang, S. 212 (2000) 476

Chian, J.H., see Lan, C.W. 212 (2000) 340

Choi, Y.D., see Nam, S. 212 (2000) 416

Christoffersen, J., see Christoffersen, M.R. 212 (2000) 500

Christoffersen, M.R., T. Balic-Zunic, S. Pehrson and J. Christoffersen, Growth and precipitation of a monoclinic calcium pyrophosphate tetrahydrate indicating auto-inhibition at pH 7 212 (2000) 500

Dai, S., see Zhao, T. 212 (2000) 451

DeMattei, R.C., see Lim, H.-J. 212 (2000) 191

Dhanasekaran, R., see Haja Hameed, A.S. 212 (2000) 227

Ding, D., see Jiang, W.H. 212 (2000) 356

Dollinger, G., see Vogg, G. 212 (2000) 148

Dong, Ch., see Shcherbak, L. 212 (2000) 385

Durbin, S.D., see Ko, J.M. 212 (2000) 155

Eliáš, P., see Kúdela, R. 212 (2000) 21

Engelhard, M., see Gao, Y. 212 (2000) 178

Fang, C., see Gu, Q. 212 (2000) 605

Feigelson, R.S., see Lim, H.-J. 212 (2000) 191

Feng, S.L., see Wang, H.L. 212 (2000) 35

Fischer, M., see Braun, N. 212 (2000) 270

Fissel, A., Thermodynamic considerations of the epitaxial growth of SiC polytypes 212 (2000) 438

0022-0248/00/$ - see front matter © 2000 Elsevier Science B.V. All rights reserved.
PII: S0022-0248(00)00394-8

Fitzpatrick, B.J., see Lin, W. 212 (2000) 83
Fu, P.-m., see Yan, X.-l. 212 (2000) 204
Fukuda, T., see Ko, J.M. 212 (2000) 155
Fukuda, T., see Chani, V.I. 212 (2000) 469

Gallagher, D.T., see Asthagiri, D. 212 (2000) 543
Gallagher, D.T., see Pan, Q. 212 (2000) 555
Gao, Y., S. Thevuthasan, D.E. McCready and M. Engelhard, MOCVD growth and structure of Nb- and V-doped TiO_2 films on sapphire 212 (2000) 178
Gębicki, W., see Kamler, G. 212 (2000) 39
Genchev, I., see Vogg, G. 212 (2000) 148
Giełzak-Kocwin, K., see Mielniczek-Brzóska, E. 212 (2000) 532
Görgens, L., see Vogg, G. 212 (2000) 148
Grahn, H.T., see Jin, S.R. 212 (2000) 56
Grosse, F. and R. Zimmermann, Monte Carlo growth simulation for $Al_xGa_{1-x}As$ heteroepitaxy 212 (2000) 128
Gu, Q., Q. Pan, X. Wu, W. Shi and C. Fang, Study on a new IR nonlinear optics crystal $CsGeCl_3$ 212 (2000) 605
Guido, L.J., see Jin, S.R. 212 (2000) 56
Gutzow, I., see Atanassova, S. 212 (2000) 233

Haja Hameed, A.S., G. Ravi, R. Dhanasekaran and P. Ramasamy, Studies on organic indole-3-aldehyde single crystals 212 (2000) 227
Hamaoka, Y., see Yan, Z. 212 (2000) 1
Han, J., see Zhang, S. 212 (2000) 217
Han, J., see Zhang, S. 212 (2000) 476
Han, Y.J., see Liu, H. 212 (2000) 391
Hasenöhrl, S., see Kúdela, R. 212 (2000) 21
Hashimoto, A., see Bhuiyan, A.G. 212 (2000) 379
Hayakawa, Y., see Iida, S. 212 (2000) 597
Hayakawa, Y., see Iida, S. 212 (2000) 601
Heng, C.L., see You, L.-p. 212 (2000) 109
Higashiyama, T., see Hu, Z.-G. 212 (2000) 368
Hirose, F., Incorporation mechanism of dopant phosphorus in the Si growth using Si_2H_6 and PH_3 212 (2000) 103
Hong, H., see Lee, J.-M. 212 (2000) 67
Hou, J.G., see Li, H.X. 212 (2000) 222
Hu, J., see Yan, X.-l. 212 (2000) 204
Hu, Z.-G., T. Higashiyama, M. Yoshimura, Y. Mori and T. Sasaki, Flux growth of the new nonlinear optical crystal: $K_2Al_2B_2O_7$ 212 (2000) 368
Huang, Q., see Liu, H. 212 (2000) 391

Iida, S., Y. Hayakawa, S. Minami, T. Koyama and M. Kumagawa, Role of lateral growth fronts in the formation of $In_xGa_{1-x}As$ bridge layer on trench substrates 212 (2000) 597
Iida, S., K. Balakrishnan, T. Koyama, Y. Hayakawa and M. Kumagawa, Growth of $In_xGa_{1-x}As$ layers with pyramidal morphology on (1 0 0)GaAs patterned substrates by liquid-phase epitaxy 212 (2000) 601
Inaba, K., see Ko, J.M. 212 (2000) 155
Inoue, T. and K. Nishioka, Effects of impurity upon the habit changes in $NaBrO_3$ crystals grown from aqueous solution 212 (2000) 507
Ishigami, R., see Bhuiyan, A.G. 212 (2000) 379

Jackson, K.A., see Shneidman, V.A. 212 (2000) 564
Jeganathan, K., R.S. Qhalid Fareed, K. Baskar, P. Ramasamy and J. Kumar, Investigations on the undersaturated liquid phase epitaxial growth of $Al_xGa_{1-x}As$ 212 (2000) 29
Jia, X., see Kimura, H. 212 (2000) 364
Jiang, W.H., H.Z. Xu, B. Xu, X.L. Ye, J. Wu, D. Ding, J.B. Liang and Z.G. Wang, Annealing effect on the surface morphology and photoluminescence of InGaAs/GaAs quantum dots grown by molecular beam epitaxy 212 (2000) 356
Jiang, W.H., see Sun, Z.Z. 212 (2000) 360
Jiang, Y.-d., see Yan, X.-l. 212 (2000) 204
Jin, S., H. Bender, L. Stalmans, R. Bilyalov, J. Poortmans, R. Loo and M. Caymax, Transmission electron microscopy investigation of the crystallographic quality of silicon films grown epitaxially on porous silicon 212 (2000) 119
Jin, S.R., M. Ramsteiner, H.T. Grahn, K.H. Ploog, Z.Q. Zhu, D.X. Shen, A.Z. Li, P. Metev and L.J. Guido, Suppression of yellow luminescence in As-doped GaN epilayers grown by metalorganic chemical vapor deposition 212 (2000) 56
Johnson, M.C., K. Poochinda, N.L. Ricker, J.W. Rogers Jr. and T.P. Pearsall, In situ monitoring and control of multicomponent gas-phase streams for growth of GaN via MOCVD 212 (2000) 11

Kakimoto, K. and H. Ozoe, Oxygen distribution at a solid–liquid interface of silicon under transverse magnetic fields 212 (2000) 429
Kamler, G., J. Zachara, S. Podsiadło, L. Adamowicz and W. Gębicki, Bulk GaN single-crystals growth 212 (2000) 39
Kang, J.-Y., see Kim, H.-S. 212 (2000) 423
Kato, H. and I. Kikuma, Effect of seed annealing on ZnSe single-crystals grown by vertical sublimation method 212 (2000) 92
Katsumata, T., see Kimura, H. 212 (2000) 364

Kawakami, S., Preparation of zirconia fibers by directional solidification of ZrO_2–Fe_3O_4 eutectic 212 (2000) 456
Khine, Y.Y., J.S. Walker and F.R. Szofran, Thermoelectric magnetohydrodynamic flow during crystal growth with a moderate or weak magnetic field 212 (2000) 584
Kikuma, I., see Kato, H. 212 (2000) 92
Kim, D.H., see Lee, J.-M. 212 (2000) 67
Kim, H.-S., K.-H. Shim, S.-Y. Lee, J.-Y. Lee and J.-Y. Kang, High-quality epitaxial growth of in situ phosphorus-doped Si films by promoting dispersion of native oxides in α-Si 212 (2000) 423
Kim, J.C., see Park, W.J. 212 (2000) 283
Kim, K.-S., H.-S. Shim and S.-H. Kim, Effect of nitrogen species and energy on the crystallinity and luminescent properties of GaN films grown by the reactive neutral beam-assisted evaporation process 212 (2000) 74
Kim, S.-H., see Kim, K.-S. 212 (2000) 74
Kim, T.W. and Y.S. Yoon, Microstructural properties of ZnO epitaxial films grown on p-InP(1 0 0) substrates at low temperature 212 (2000) 411
Kimura, H., X. Jia, K. Shoji, R. Sakai and T. Katsumata, Crystal growth of $Ba(B_{1-x}Al_x)_2O_4$ using a new Fz furnace with double ring-shaped halogen lamp heater 212 (2000) 364
Kishimoto, D., T. Nishinaga, S. Naritsuka, T. Noda, Y. Nakamura and H. Sakaki, (1 1 1)B growth elimination in GaAs MBE of (0 0 1)-(1 1 1)B mesa structure by suppressing 2D-nucleation 212 (2000) 373
Kleijn, C.R., see Van Santen, H. 212 (2000) 299
Kleijn, C.R., see Van Santen, H. 212 (2000) 311
Ko, J.M., K. Inaba, S.D. Durbin and T. Fukuda, Surface characterization of NdF_3 layers on Si(1 1 1) substrates grown by molecular beam epitaxy 212 (2000) 155
Kojima, H., see Maljuk, A. 212 (2000) 138
Kong, M.Y., see Zhuang, Q.D. 212 (2000) 352
Kopach, O., see Shcherbak, L. 212 (2000) 385
Kowach, G.R., Growth of single crystals of ZrW_2O_8 212 (2000) 167
Koyama, T., see Iida, S. 212 (2000) 597
Koyama, T., see Iida, S. 212 (2000) 601
Kozhemyakin, G.N., see Zemskov, V.S. 212 (2000) 161
Kubota, N., M. Yokota and J.W. Mullin, The combined influence of supersaturation and impurity concentration on crystal growth 212 (2000) 480
Kučera, M., see Kúdela, R. 212 (2000) 21
Kúdela, R., M. Kučera, B. Olejníková, P. Eliáš, S. Hasenöhrl and J. Novák, Formation of interfaces in InGaP/GaAs/InGaP quantum wells 212 (2000) 21
Kukli, K., M. Ritala, R. Matero and M. Leskelä, Influence of atomic layer deposition parameters on the phase content of Ta_2O_5 films 212 (2000) 459
Kumagawa, M., see Iida, S. 212 (2000) 597
Kumagawa, M., see Iida, S. 212 (2000) 601
Kumar, J., see Jeganathan, K. 212 (2000) 29

Lai, W., see Xu, M. 212 (2000) 291
Lai, Y.-J. and J.-C. Chen, The influence of heavy iron-doping on $LiNbO_3$ fibers and their growth 212 (2000) 211
Lam, C., see Zhang, Y.F. 212 (2000) 115
Lan, C.W., M.C. Liang and J.H. Chian, Influence of ampoule rotation on three-dimensional convection and segregation in Bridgman crystal growth under imperfect growth conditions 212 (2000) 340
Lee, C.S., see Zhang, Y.F. 212 (2000) 115
Lee, J.-M., D.H. Kim, H. Hong, J.-C. Woo and S.-J. Park, Growth of InAs nanocrystals on GaAs(1 0 0) by droplet epitaxy 212 (2000) 67
Lee, J.-Y., see Kim, H.-S. 212 (2000) 423
Lee, J.W., see Nam, S. 212 (2000) 416
Lee, K.-S., see Nam, S. 212 (2000) 416
Lee, S.T., see Lu, H.B. 212 (2000) 173
Lee, S.T., see Zhang, Y.F. 212 (2000) 115
Lee, S.-Y., see Kim, H.-S. 212 (2000) 423
Lee, Z.H., see Park, W.J. 212 (2000) 283
Lenhoff, A.M., see Asthagiri, D. 212 (2000) 543
Leskelä, M., see Kukli, K. 212 (2000) 459
Li, A.Z., see Jin, S.R. 212 (2000) 56
Li, H.X., M.Z. Lin and J.G. Hou, Electrophoretic deposition of ligand-stabilized silver nanoparticles synthesized by the process of photochemical reduction 212 (2000) 222
Li, J.M., see Zhuang, Q.D. 212 (2000) 352
Li, S.F., see Sun, X.L. 212 (2000) 397
Li, Y.-F., see Sun, Z.-Z. 212 (2000) 360
Li, Z., see Liu, H. 212 (2000) 391
Li Zhengdong, see Yang Shangfeng 212 (2000) 372
Liang, J.B., see Jiang, W.H. 212 (2000) 356
Liang, M.C., see Lan, C.W. 212 (2000) 340
Lim, H.-J., R.C. DeMattei, R.S. Feigelson and K. Rochford, Striations in YIG fibers grown by the laser-heated pedestal method 212 (2000) 191
Lin, F., see Sun, Z.-Z. 212 (2000) 360
Lin, L.Y., see Zhuang, Q.D. 212 (2000) 352
Lin, M.Z., see Li, H.X. 212 (2000) 222

Lin, W., M.C. Tamargo, J. Steiner, H.-Y. Wei, W. Sarney, L. Salamanca-Riba and B.J. Fitzpatrick, Growth and characterization of hexagonal (Zn,Mg)(S,Se) bulk substrates 212 (2000) 83
Liu, F.-Q., see Sun, Z.-Z. 212 (2000) 360
Liu, H., H. Chen, Li, Wan, Q. Huang, J. Zhou, N. Yang, K. Tao, Y.J. Han and Y. Luo, Growth and properties of hexagonal GaN on GaAs(0 0 1) substrate by RF-molecular beam epitaxy using an AlAs nucleation layer 212 (2000) 391
Liu, J., see Zhang, S. 212 (2000) 476
Loo, R., see Jin, S. 212 (2000) 119
Lu, H., see Zhao, T. 212 (2000) 451
Lu, H.B., N. Wang, W.Z. Chen, F. Chen, T. Zhao, H.Y. Peng, S.T. Lee and G.Z. Yang, Laser molecular beam epitaxy of $BaTiO_3$ and $SrTiO_3$ ultra thin films 212 (2000) 173
Lu, T., see Balitsky, V.S. 212 (2000) 255
Lui, P.Y., see Yoon, S.F. 212 (2000) 49
Luo, G., see Xu, M. 212 (2000) 291
Luo, Y., see Liu, H. 212 (2000) 391

Ma, S.Y., see You, L.-p. 212 (2000) 109
Ma, Z.C., see You, L.-p. 212 (2000) 109
Machida, H., see Chani, V.I. 212 (2000) 469
Machina, I.B., see Balitsky, V.S. 212 (2000) 255
Mai, Z., see Xu, M. 212 (2000) 291
Maljuk, A., S. Watauchi, I. Tanaka and H. Kojima, The effect of B_2O_3 addition on $La_{2-x}Sr_xCuO_4$ single-crystal growth 212 (2000) 138
Mao Binguei, see Yang Shangfeng 212 (2000) 372
Mar'in, A.A., see Balitsky, V.S. 212 (2000) 255
Maruyama, S. and H. Ooshima, Crystallization behavior of taltirelin polymorphs in a mixture of water and methanol 212 (2000) 239
Matero, R., see Kukli, K. 212 (2000) 459
Matsuda, A., see Sekar, C. 212 (2000) 142
McCready, D.E., see Gao, Y. 212 (2000) 178
Metev, P., see Jin, S.R. 212 (2000) 56
Mielniczek-Brzóska, E., K. Giełzak-Koćwin and K. Sangwal, Effect of Cu(II) ions on the growth of ammonium oxalate monohydrate crystals from aqueous solutions: growth kinetics, segregation coefficient and characterisation of incorporation sites 212 (2000) 532
Minami, S., see Iida, S. 212 (2000) 597
Mohan, R., K.A. Boateng and A.S. Myerson, Estimation of crystal growth kinetics using differential scanning calorimetry 212 (2000) 489
Moon, Y. and E. Yoon, Effects of PH_3/H_2 purge on the As concentration profile of $InAs_xP_{1-x}/InP$ single quantum wells 212 (2000) 61
Mori, Y., see Hu, Z.-G. 212 (2000) 368
Müller, G., see Vizman, D. 212 (2000) 334
Mullin, J.W., see Kubota, N. 212 (2000) 480
Myerson, A.S., see Mohan, R. 212 (2000) 489

Nakamura, Y., see Kishimoto, D. 212 (2000) 373
Nam, S., Y.-M. Yu, J. Rhee, B. O, K.-S. Lee, Y.D. Choi, J.W. Lee and S. Sakakibara, GaAs substrate thermal preheating effect exerted on ZnTe epilayer 212 (2000) 416
Nancollas, G.H., see Tang, R. 212 (2000) 261
Nanev, Chr.N., Polyhedral (in-)stability by increasing supersaturation – maximum rate of stable growth 212 (2000) 516
Naritsuka, S., see Yan, Z. 212 (2000) 1
Naritsuka, S., see Kishimoto, D. 212 (2000) 373
Neykov, K., see Atanassova, S. 212 (2000) 233
Nicoara, I., see Vizman, D. 212 (2000) 334
Nishinaga, T., see Yan, Z. 212 (2000) 1
Nishinaga, T., see Kishimoto, D. 212 (2000) 373
Nishioka, K., see Inoue, T. 212 (2000) 507
Nishizawa, J.-i., see Oyama, Y. 212 (2000) 402
Noda, T., see Kishimoto, D. 212 (2000) 373
Novák, J., see Kúdela, R. 212 (2000) 21

O, B., see Nam, S. 212 (2000) 416
Olejníková, B., see Kúdela, R. 212 (2000) 21
Ooshima, H., see Maruyama, S. 212 (2000) 239
Oyama, Y., J.-i. Nishizawa, K. Seo and K. Suto, Electrical activation of Te and Se in GaAs at extremely heavy doping up to $5 \times 10^{20}\,cm^{-3}$ prepared by intermittent injection of TEG/AsH_3 in ultrahigh vacuum 212 (2000) 402
Ozoe, H., see Kakimoto, K. 212 (2000) 429

Pałczyńska, T., see Sangwal, K. 212 (2000) 522
Pan, Q. and D.T. Gallagher, Probing protein interaction chemistry through crystal growth: structure, mutation, and mechanism in subtilisin s88 212 (2000) 555
Pan, Q., see Gu, Q. 212 (2000) 605
Park, S.-J., see Lee, J.-M. 212 (2000) 67
Park, W.J., J.C. Kim, B.J. Ye and Z.H. Lee, Macrosegregation in Bridgman growth of Terfenol-D and effects of annealing 212 (2000) 283
Pearsall, T.P., see Johnson, M.C. 212 (2000) 11
Pehrson, S., see Christoffersen, M.R. 212 (2000) 500
Peng, H.Y., see Lu, H.B. 212 (2000) 173
Plevachuk, Yu., see Shcherbak, L. 212 (2000) 385
Ploog, K.H., see Jin, S.R. 212 (2000) 56
Podsiadło, S., see Kamler, G. 212 (2000) 39
Poochinda, K., see Johnson, M.C. 212 (2000) 11
Poortmans, J., see Jin, S. 212 (2000) 119
Popov, D.I., L.L. Regel and W.R. Wilcox, One-dimensional phase-field model for binary alloys 212 (2000) 574

Qhalid Fareed, R.S., see Jeganathan, K. 212 (2000) 29
Qin, G.G., see You, L.-p. 212 (2000) 109
Qiu, J.-l., see Yan, X.-l. 212 (2000) 204

Ramasamy, P., see Jeganathan, K. 212 (2000) 29
Ramasamy, P., see Haja Hameed, A.S. 212 (2000) 227
Ramasamy, P., see Srinivasan, K. 212 (2000) 246
Ramsteiner, M., see Jin, S.R. 212 (2000) 56
Ratke, L., see Stöcker, C. 212 (2000) 324
Ravi, G., see Haja Hameed, A.S. 212 (2000) 227
Regel, L.L., see Popov, D.I. 212 (2000) 574
Rhee, J., see Nam, S. 212 (2000) 416
Ricker, N.L., see Johnson, M.C. 212 (2000) 11
Ritala, M., see Kukli, K. 212 (2000) 459
Rochford, K., see Lim, H.-J. 212 (2000) 191
Rogers Jr., J.W., see Johnson, M.C. 212 (2000) 11
Rossman, G.R., see Balitsky, V.S. 212 (2000) 255

Sakai, R., see Kimura, H. 212 (2000) 364
Sakaki, H., see Kishimoto, D. 212 (2000) 373
Sakakibara, S., see Nam, S. 212 (2000) 416
Salamanca-Riba, L., see Lin, W. 212 (2000) 83
Sangwal, K. and T. Pałczyńska, On the supersaturation and impurity concentration dependence of segregation coefficient in crystals grown from solutions 212 (2000) 522
Sangwal, K., see Mielniczek-Brzóska, E. 212 (2000) 532
Sankaranarayanan, K., see Srinivasan, K. 212 (2000) 246
Sarney, W., see Lin, W. 212 (2000) 83
Sasaki, T., see Hu, Z.-G. 212 (2000) 368
Sawada, T. and K. Takemura, Pressure-induced faceting in an NH_4Cl crystal 212 (2000) 512
Sekar, C., T. Watanabe and A. Matsuda, Crystal growth and characterization of the 4-leg spin ladder compound $La_2Cu_2O_5$ 212 (2000) 142
Seo, K., see Oyama, Y. 212 (2000) 402
Shao, Z., see Zhang, S. 212 (2000) 476
Shcherbak, L., O. Kopach, Yu. Plevachuk, V. Sklyarchuk, Ch. Dong and P. Siffert, The viscosity of liquid cadmium telluride 212 (2000) 385
Shen, D.X., see Jin, S.R. 212 (2000) 56
Shi, W., see Gu, Q. 212 (2000) 605
Shigley, J.E., see Balitsky, V.S. 212 (2000) 255
Shim, H.-S., see Kim, K.-S. 212 (2000) 74
Shim, K.-H., see Kim, H.-S. 212 (2000) 423
Shneidman, V.A., K.A. Jackson and K.M. Beatty, Non-equilibrium interface of a two-dimensional low-temperature crystal 212 (2000) 564
Shoji, K., see Kimura, H. 212 (2000) 364
Siffert, P., see Shcherbak, L. 212 (2000) 385
Sklyarchuk, V., see Shcherbak, L. 212 (2000) 385
Srinivasan, K., K. Sankaranarayanan, S. Thangavelu and P. Ramasamy, Influence of organic solvents on the habit of NMBA (4-nitro-4′-methyl benzylidene aniline) crystals 212 (2000) 246
Stalmans, L., see Jin, S. 212 (2000) 119
Steiner, J., see Lin, W. 212 (2000) 83
Stöcker, C. and L. Ratke, Monotectic composite growth with fluid flow 212 (2000) 324
Stutzmann, M., see Vogg, G. 212 (2000) 148
Su Genbo, see Yang Shangfeng 212 (2000) 372
Sun, L., see Zhang, S. 212 (2000) 217
Sun, X.L., H. Yang, Y.T. Wang, L.X. Zheng, D.P. Xu, D.G. Zhao, S.F. Li and Z.G. Wang, Effect of buffer layer growth conditions on the secondary hexagonal phase content in cubic GaN films on GaAs(0 0 1) substrates 212 (2000) 397
Sun, Z.-Z., J. Wu, F. Lin, F.-Q. Liu, Y.-H. Chen, X.-L. Ye, W.-H. Jiang, Y.-F. Li, B. Xu and Z.-G. Wang, The structural and photoluminescence properties of self-organized quantum dots in $InAs/In_{0.53}Ga_{0.47}As$ multilayer on InP substrate 212 (2000) 360
Suto, K., see Oyama, Y. 212 (2000) 402
Szofran, F.R., see Khine, Y.Y. 212 (2000) 584

Tack, J., see Braun, N. 212 (2000) 270
Takemura, K., see Sawada, T. 212 (2000) 512
Tamargo, M.C., see Lin, W. 212 (2000) 83
Tanaka, I., see Maljuk, A. 212 (2000) 138
Tang Jing, see Yang Shangfeng 212 (2000) 372
Tang, R. and G.H. Nancollas, Abnormal dissolution of octacalcium phosphate crystals at constant undersaturation 212 (2000) 261
Tang, Y.H., see Zhang, Y.F. 212 (2000) 115
Tao, K., see Liu, H. 212 (2000) 391
Thangavelu, S., see Srinivasan, K. 212 (2000) 246
Thevuthasan, S., see Gao, Y. 212 (2000) 178

Ueng, H.Y., see Yokoyama, M. 212 (2000) 97

Van Den Akker, H.E.A., see Van Santen, H. 212 (2000) 299
Van Den Akker, H.E.A., see Van Santen, H. 212 (2000) 311
Van Santen, H., C.R. Kleijn and H.E.A. Van Den Akker, On turbulent flows in cold-wall CVD reactors 212 (2000) 299
Van Santen, H., C.R. Kleijn and H.E.A. Van Den Akker, Symmetry breaking in a stagnation-flow CVD reactor 212 (2000) 311
Vizman, D., I. Nicoara and G. Müller, Effects of temperature asymmetry and tilting in the vertical Bridgman growth of semi-transparent crystals 212 (2000) 334

Vogg, G., M.S. Brandt, M. Stutzmann, I. Genchev, A. Bergmaier, L. Görgens and G. Dollinger, Epitaxial $CaGe_2$ films on germanium 212 (2000) 148

Walker, J.S., see Khine, Y.Y. 212 (2000) 584
Wan, L., see Liu, H. 212 (2000) 391
Wang, D., see Xu, M. 212 (2000) 291
Wang, H.L., F.H. Yang and S.L. Feng, Photoluminescence in Si and Be directly doped self-organized InAs/GaAs quantum dots 212 (2000) 35
Wang, N., see Zhang, Y.F. 212 (2000) 115
Wang, N., see Lu, H.B. 212 (2000) 173
Wang, Q., see Zhang, S. 212 (2000) 217
Wang, X.-m., see Yan, X.-l. 212 (2000) 204
Wang, Y.T., see Sun, X.L. 212 (2000) 397
Wang, Z.G., see Jiang, W.H. 212 (2000) 356
Wang, Z.G., see Sun, Z.Z. 212 (2000) 360
Wang, Z.G., see Sun, X.L. 212 (2000) 397
Watanabe, T., see Sekar, C. 212 (2000) 142
Watauchi, S., see Maljuk, A. 212 (2000) 138
Wei, H.-Y., see Lin, W. 212 (2000) 83
Weinkauf, S., see Braun, N. 212 (2000) 270
Wilcox, W.R., see Popov, D.I. 212 (2000) 574
Woo, J.-C., see Lee, J.-M. 212 (2000) 67
Wu, J., see Jiang, W.H. 212 (2000) 356
Wu, J., see Sun, Z.-Z. 212 (2000) 360
Wu Jianmin, see Yang Shangfeng 212 (2000) 372
Wu, X., see Yan, X.-l. 212 (2000) 204
Wu, X., see Gu, Q. 212 (2000) 605
Wu, Z., see Xu, M. 212 (2000) 291
Wu, Z.-l., see You, L.-p. 212 (2000) 109

Xu, B., see Jiang, W.H. 212 (2000) 356
Xu, B., see Sun, Z.-Z. 212 (2000) 360
Xu, D.P., see Sun, X.L. 212 (2000) 397
Xu, H.Z., see Jiang, W.H. 212 (2000) 356
Xu, M., G. Luo, C. Chai, Z. Mai, W. Lai, Z. Wu and D. Wang, Effect of annealing on the microstructure of $Ni_{80}Fe_{20}$/Cu multilayers 212 (2000) 291

Yamamoto, A., see Bhuiyan, A.G. 212 (2000) 379
Yan, X.-l., X. Wu, J.-f. Zhou, Z.-g. Zhang, X.-m. Wang, P.-m. Fu, Y.-d. Jiang, J. Hu and J.-l. Qiu, Growth of Tm : Ho : YVO_4 laser single crystals by the floating zone method 212 (2000) 204
Yan, Z., Y. Hamaoka, S. Naritsuka and T. Nishinaga, Coalescence in microchannel epitaxy of InP 212 (2000) 1
Yang, F.H., see Wang, H.L. 212 (2000) 35
Yang, G., see Zhao, T. 212 (2000) 451
Yang, G.Z., see Lu, H.B. 212 (2000) 173
Yang, H., see Sun, X.L. 212 (2000) 397
Yang, N., see Liu, H. 212 (2000) 391
Yang Shangfeng, Su Genbo, Tang Jing, Mao Bingwei, Wu Jianmin, Li Zhengdong, Erratum to "Surface topography of rapidly grown KH PO crystals with additives: ex situ investigation by atomic force microscopy". [J. Crystal Growth 203 (1999) 425–433] 212 (2000) 372
Ye, B.J., see Park, W.J. 212 (2000) 283
Ye, X.L., see Jiang, W.H. 212 (2000) 356
Ye, X.L., see Sun, Z.Z. 212 (2000) 360
Yokota, M., see Kubota, N. 212 (2000) 480
Yokoyama, M., N.T. Chen and H.Y. Ueng, Growth and characterization of ZnSe on Si by atomic layer epitaxy 212 (2000) 97
Yoon, E., see Moon, Y. 212 (2000) 61
Yoon, S.F., P.Y. Lui and H.Q. Zheng, Characterization of $Ga_{0.52}In_{0.48}P$/GaAs single quantum well structures grown by solid source molecular beam epitaxy using deep level transient spectroscopy 212 (2000) 49
Yoon, S.F., see Zhuang, Q.D. 212 (2000) 352
Yoon, Y.S., see Kim, T.W. 212 (2000) 411
Yoshikawa, A., see Chani, V.I. 212 (2000) 469
Yoshimura, M., see Hu, Z.-G. 212 (2000) 368
You, L.-p., Y., C.L. Heng, S.Y. Ma, Z.C. Ma, W.H. Zong, Z.-l. Wu and G.G. Qin, Precipitation and crystallization of nanometer Si clusters in annealed Si-rich SiO_2 films 212 (2000) 109
Yu, Y.-M., see Nam, S. 212 (2000) 416

Zachara, J., see Kamler, G. 212 (2000) 39
Zemskov, V.S., A.D. Belaya, U.S. Beluy and G.N. Kozhemyakin, Growth and investigation of thermoelectric properties of Bi–Sb alloy single crystals 212 (2000) 161
Zeng, Y.P., see Zhuang, Q.D. 212 (2000) 352
Zhang, S., Z. Cheng, J. Han, L. Sun, X. Zhang, S. Zhao, Q. Wang and H. Chen, Growth of $Nd_xGd_{1-x}Ca_4O(BO_3)_3$ along phase-matching direction and passive mode-locking self-frequency-doubling characteristics 212 (2000) 217
Zhang, S., Z. Cheng, J. Liu, J. Han, Z. Shao and H. Chen, Growth and second-harmonic-generation of Bi^{3+}- or Li^+-doped $GdCa_4O(BO_3)_3$ crystals 212 (2000) 476
Zhang, X., see Zhang, S. 212 (2000) 217
Zhang, Y.F., Y.H. Tang, C. Lam, N. Wang, C.S. Lee, I. Bello and S.T. Lee, Bulk-quantity Si nanowires synthesized by SiO sublimation 212 (2000) 115
Zhang, Z.-g., see Yan, X.-l. 212 (2000) 204
Zhao, D.G., see Sun, X.L. 212 (2000) 397
Zhao, S., see Zhang, S. 212 (2000) 217
Zhao, T., see Lu, H.B. 212 (2000) 173

Zhao, T., H. Lu, F. Chen, S. Dai, G. Yang and Z. Chen, Highly conductive Nb doped $SrTiO_3$ epitaxial thin films grown by laser molecular beam epitaxy 212 (2000) 451
Zheng, H.Q., see Yoon, S.F. 212 (2000) 49
Zheng, H.Q., see Zhuang, Q.D. 212 (2000) 352
Zheng, L.X., see Sun, X.L. 212 (2000) 397
Zhou, J. see Liu, H. 212 (2000) 391
Zhou, J.-f., see Yan, X.-l. 212 (2000) 204
Zhu, Z.Q., see Jin, S.R. 212 (2000) 56
Zhuang, Q.D., J.M. Li, Y.P. Zeng, S.F. Yoon, H.Q. Zheng, M.Y. Kong and L.Y. Lin, Effect of rapid thermal annealing on InGaAs/GaAs quantum wells 212 (2000) 352
Zimmermann, R., see Grosse, F. 212 (2000) 128
Zong, W.H., see You, L.-p. 212 (2000) 109

ELSEVIER

Journal of Crystal Growth 212 (2000) 615–616

JOURNAL OF CRYSTAL GROWTH

www.elsevier.nl/locate/jcrysgro

Subject index

Computer simulation
- of aluminum gallium arsenide heteroepitaxy 128
- of Bridgman growth 340
- of fluid dynamics 311
- of nickel iron copper multilayers growth 291
- of solidification 574
- of supersaturation 480
- of turbulent flow in chemical vapor deposition 299
Convection 211, 324, 334, 584

Dendritic growth
- of lanthanum copper oxide 142
Device characterization
- electronic materials 119
- quantum wells 21, 35, 49, 61, 352
- quantum wires and dots 115, 356, 360
Diffusional control
- of indium arsenide 67
- of protein crystal growth 543

Electronic materials, see Device characterization
Epitaxy, see Thin film growth
Etching
- chemical 227, 416

Heat flow control
- of silicon 429
Hydrodynamics, see Convection

Kinetics
- of growth 178, 255, 261, 324, 360, 489, 500, 516, 522, 532, 543, 555, 564
- of interface control 61, 291, 564
- of nucleation 67, 178, 233

Lasers, crystals for
- gadolinium calcium oxyborate 217

Melt growth technique
- by Bridgman–Stockbarger method
- - of cadmium telluride 385
- - of terfenol-D 283
- by Czochralski method
- - of bismuth antimonide 161
- - of gadolinium calcium oxyborate 217, 476
- - of silicon 429
- by floating zone method
- - of barium borate aluminate 364
- - of yttrium iron garnet 191
- - of yttrium vanadate 191
- - of zirconia 456
- by micro pulling down method
- - of terbium aluminum garnet 469
- by zone melting
- - of zinc manganese sulphide selenide 83
Microgravity growth 584
Morphological stability
- of protein 555

Nucleation
- of calcium oxalate 261
- of protein crystals 270
Numbers
- Marangoni 211
- Peclet 334
- Rayleigh 334, 340

Phase diagram
- of lanthanum oxide–copper oxide 142

Quantum wells, see Device characterization
Quantum wires and dots, see Device characterization

Solution growth technique
- by flux method
- - of potassium aluminum borate 368
- - of zirconium tungstate 167
- - of zirconium tungstate oxide 167
- by low temperature method
- - of ammonium oxalate monohydrate 532
- - of calcium oxalate calculi 233
- - of cesium germanium chloride 605
- - of 4-nitro-4-methyl benzylidene aniline 246
- - of ligand stabilized silver nanoparticles 222
- - of organic indole-3-aldehyde 227
- - of sodium borate 507
- - of taltirelin polymorphs 239

0022-0248/00/$ - see front matter © 2000 Elsevier Science B.V. All rights reserved.
PII: S0022-0248(00)00395-X

Stefan problem or moving boundary problem
- of monotectics 324
Superconductivity materials, high T_c
- - of lanthanum copper oxide 142
- - of lanthanum strontium copper oxide 138
Superlattices, multilayers
- of barium titanate 173
- of strontium titanate 173
Surface energy, determination
- of calcium phosphate 261
Surface structure
- of ametrine 255
- of ammonium chloride 512
- of barium titanate 173
- of protein crystals 270
- of strontium titanate 173
- of tantalum oxide 459

Thin film growth, epitaxy
- by atomic layer epitaxy
- - of gallium arsenide 402
- - of tantalum oxide 459
- - of zinc selenide 97
- by liquid phase epitaxy
- - of aluminum gallium arsenide 29
- - of indium gallium arsenide 597, 601
- - of indium phosphide 1
- by magnetron sputtering
- - of silicon clusters 109
- by metalorganic molecular beam epitaxy
- - of gallium nitride 397
- by molecular beam epitaxy
- - of aluminum gallium arsenide 128
- - of barium titanate 173
- - of gallium arsenide 35, 373
- - of gallium indium phosphide 49
- - of gallium nitride 391
- - of indium arsenide 35, 67, 360, 391
- - of indium gallium arsenide 352, 356, 360
- - of neodymium trifluoride 155
- - of silicon carbide 438
- - of strontium titanate 173, 451
- - theory of silicon carbide polytype growth 438
- by reactive deposition epitaxy
- - of calcium digermanide 148
- by vapor phase epitaxy
- - through chemical vapor deposition
- - - of gallium nitride 74
- - - of porous silicon 119
- - - of silicon 423
- - through evaporation and condensation
- - - of silicon nanowires 115
- - - of zinc oxide 411
- - - of zinc selenide 92
- - through metalorganic chemical vapor deposition
- - - of gallium nitride 11, 56
- - - of gallium phosphide 379
- - - of indium arsenide phosphide 61
- - - of indium gallium phosphide 21
- - - of indium nitride 379
- - - of titanium oxide 178
- - theory of doping 103

Vapor growth technique
- by evaporation and condensation
- - of gallium nitride 39